N-Channel Enhancement Mode Power MOSFET

Description

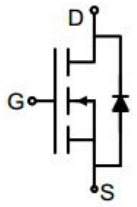
The GT007N04TL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

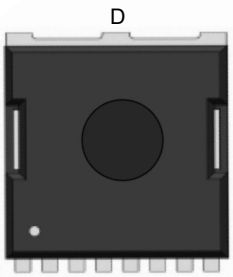
- V_{DS} 40V
- I_D (at V_{GS} = 10V) 150A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 1.5mΩ
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 2mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



G_1 S_2 S_3 S_4 S_5 S_6 S_7 S_8

TOLL

Ordering Information

Device	Package	Marking	Packaging
GT007N04TL	TOLL-8L	GT007N04	1800pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Continuous Drain Current	I_D	150	A
Pulsed Drain Current (note1)	I_{DM}	600	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	156	W
Single pulse avalanche energy （note2）	E_{AS}	361	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	ºC/W
Maximum Junction-to-Case	R_{thJC}	0.8	ºC/W

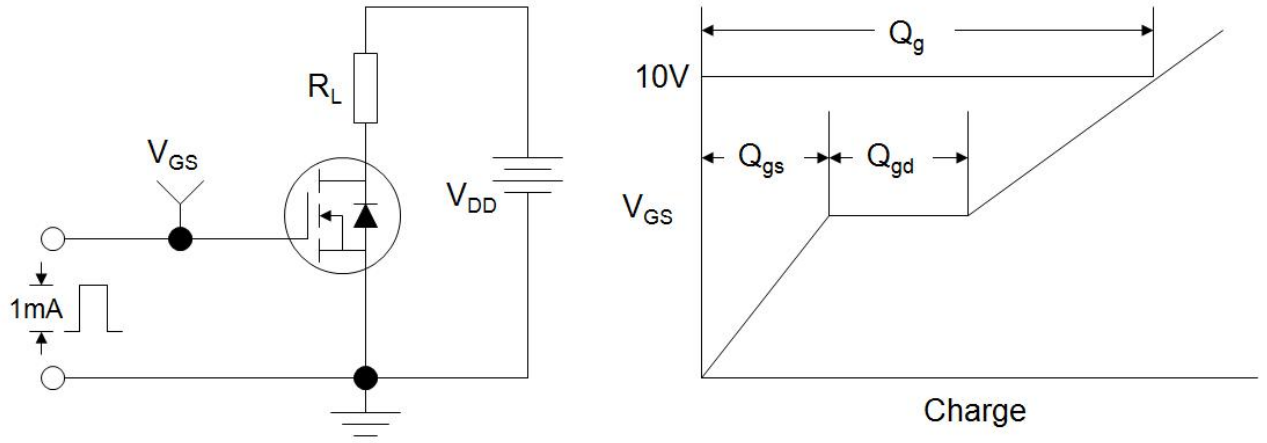
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 30A	--	1.2	1.5	mΩ
		V_{GS} = 4.5V, I_D = 30A	--	1.6	2	
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 30A	--	86	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 20V, f = 1.0MHz	--	7363	--	pF
Output Capacitance	C_{oss}		--	1842	--	
Reverse Transfer Capacitance	C_{rss}		--	1511	--	
Total Gate Charge	Q_g	V_{DD} = 20V, I_D = 20A, V_{GS} = 10V	--	163	--	nC
Gate-Source Charge	Q_{gs}		--	22	--	
Gate-Drain Charge	Q_{gd}		--	33	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 20V, I_D = 20A, R_G = 3Ω	--	13	--	ns
Turn-on Rise Time	t_r		--	18	--	
Turn-off Delay Time	$t_{d(off)}$		--	135	--	
Turn-off Fall Time	t_f		--	52	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	150	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 30A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 20A, V_{GS} = 0V di/dt=500A/us	--	78	--	nC
Reverse Recovery Time	Trr		--	26	--	ns

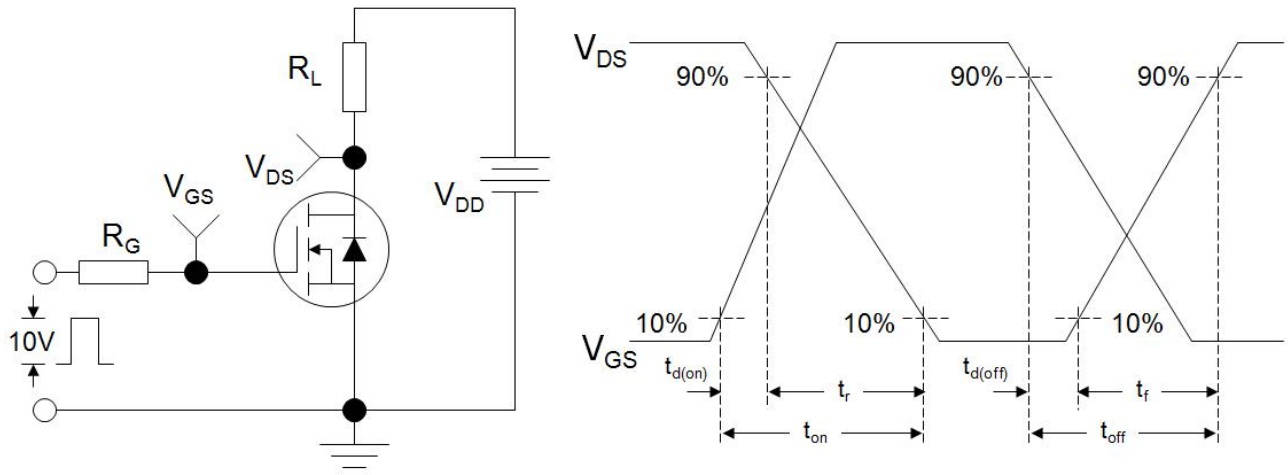
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=40V,VGS=10V,L=0.5mH,Rg=25Ω
3. Identical low side and high side switch with identical R_G

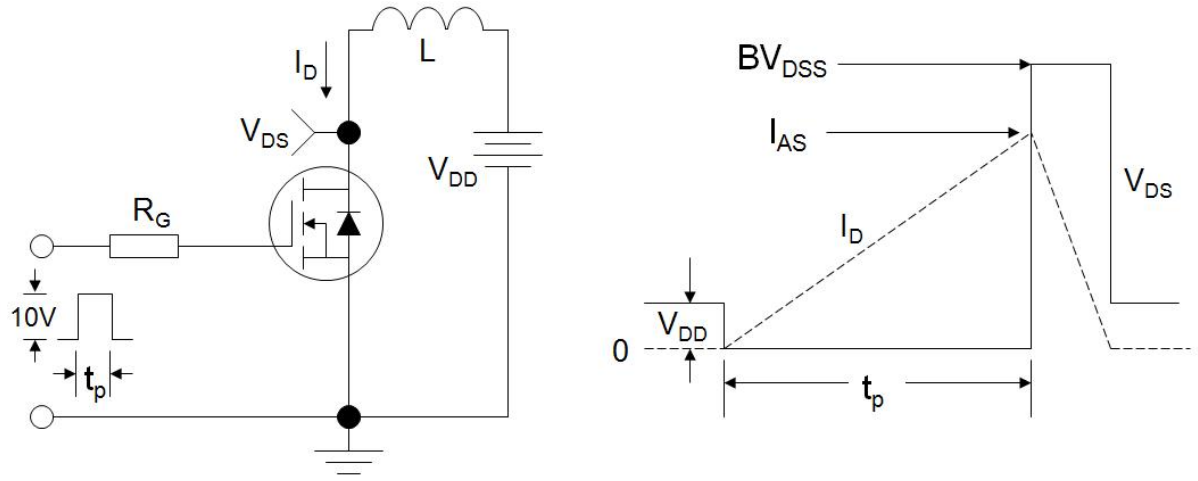
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

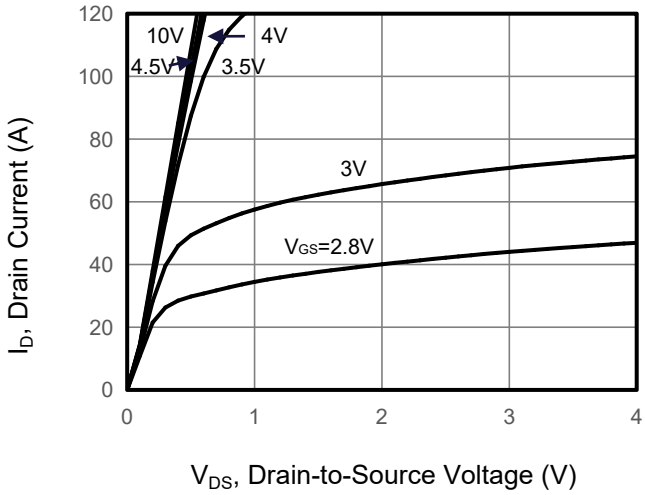


Figure 2. Transfer Characteristics

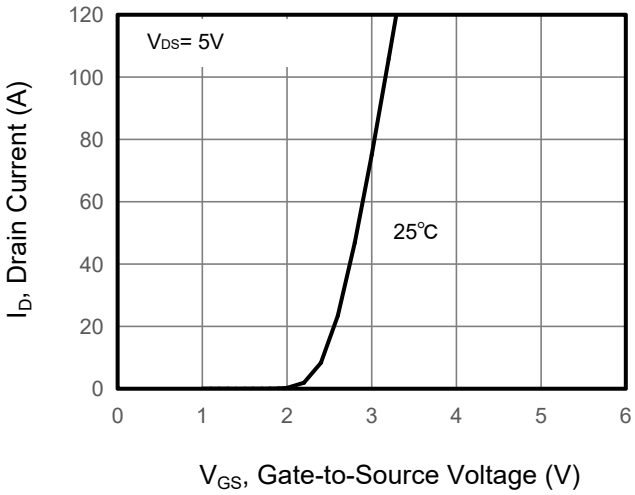


Figure 3. Drain Source On Resistance

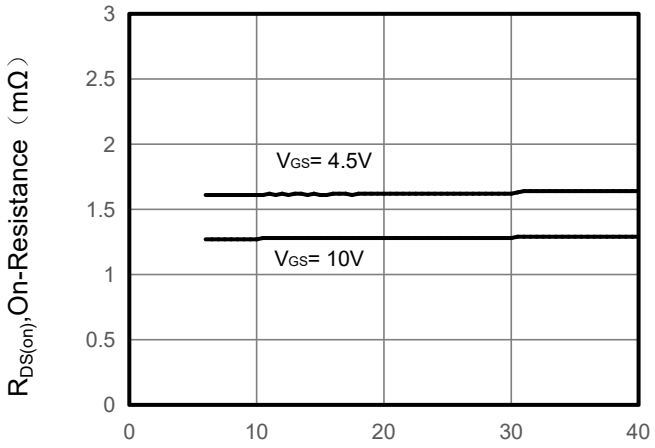


Figure 4. Gate Charge

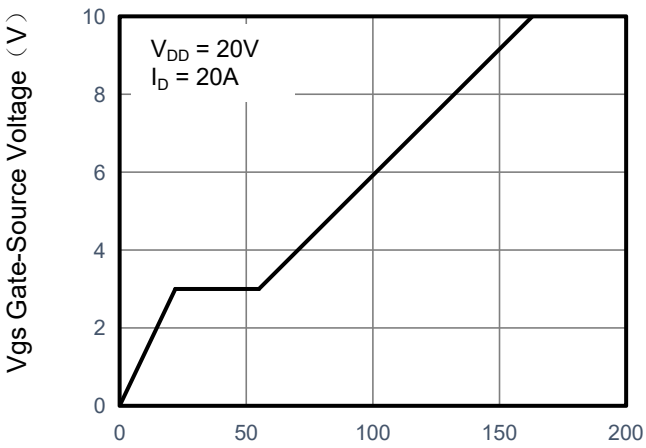


Figure 5. Capacitance

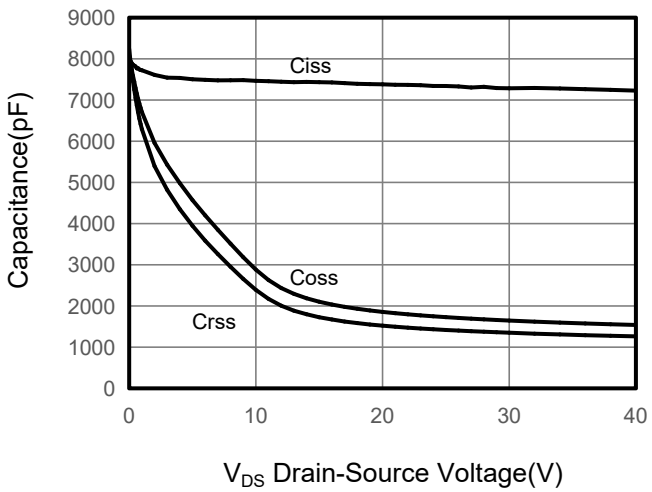
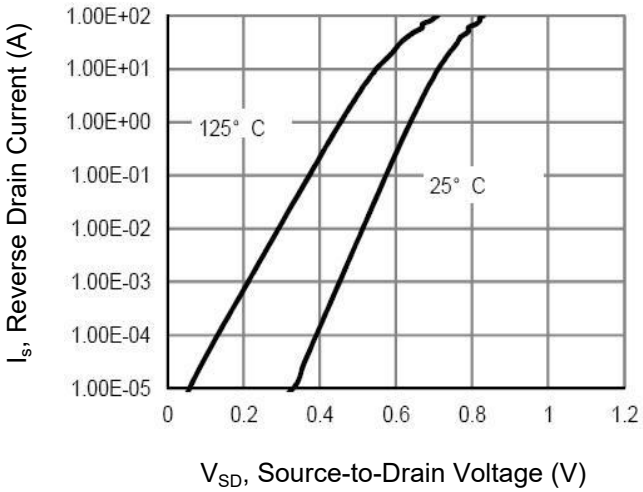


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

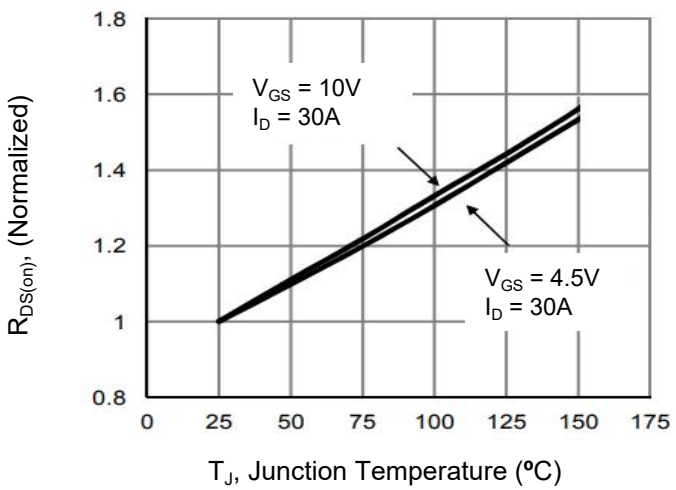


Figure 8. Safe Operation Area

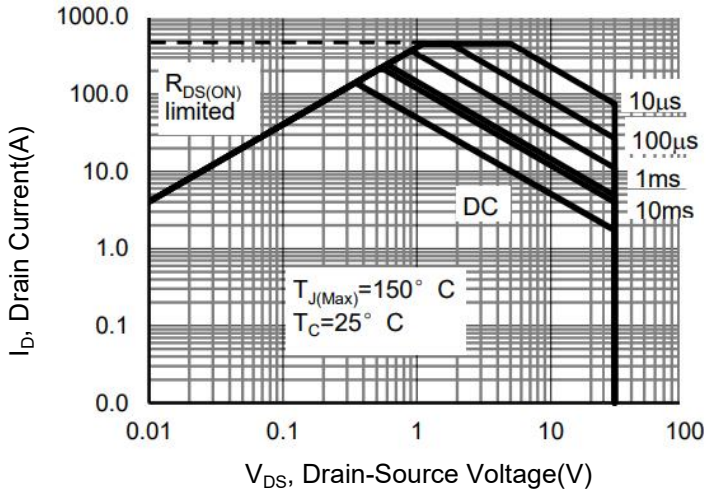
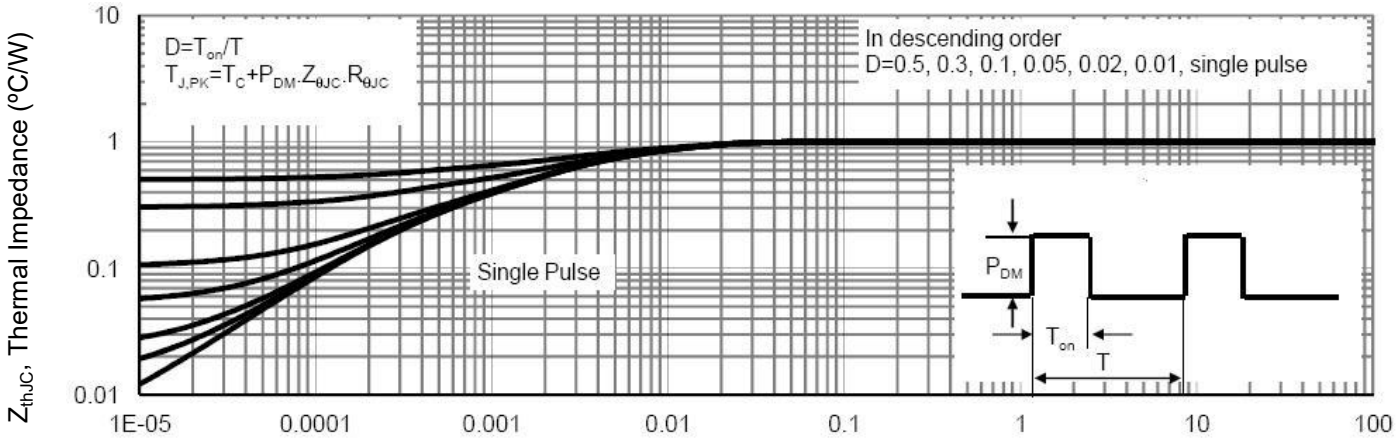
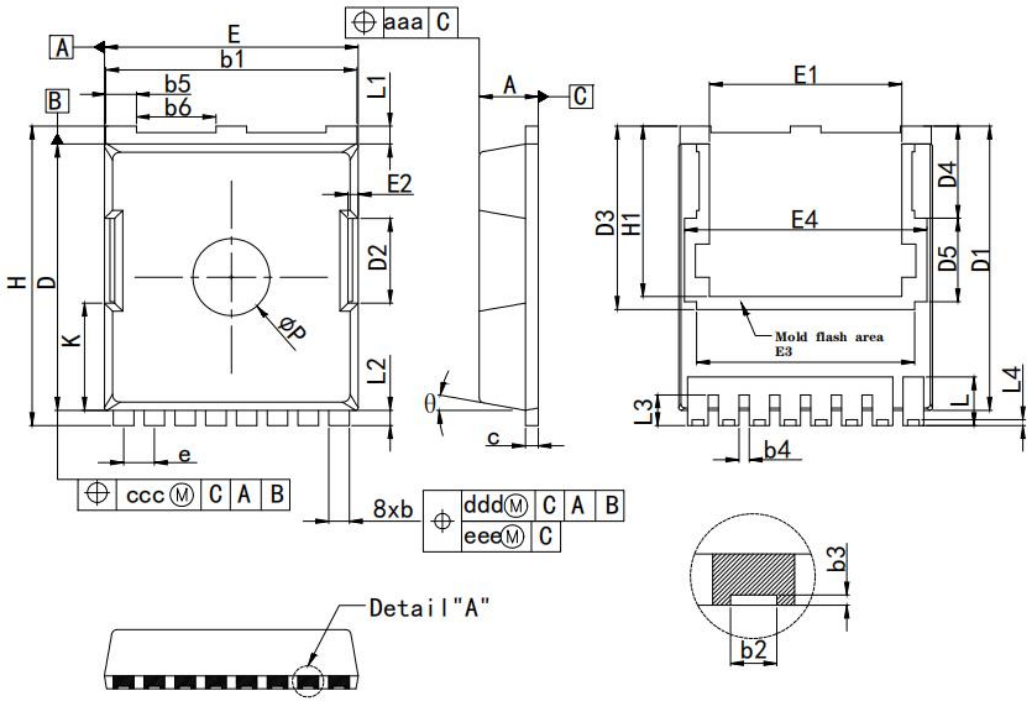


Figure 9. Normalized Maximum Transient Thermal Impedance



TOLL Package Information



SYMBOL	COMMON		
	MILLIMETER		
	MIN	NOMINAL	MAX
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.36	0.45	0.55
b3	0.05	0.100	/
b4	0.30	0.40	0.50
b5	1.10	1.20	1.30
b6	3.00	3.10	3.20
c	0.40	0.50	0.60
D	10.28	10.38	10.55
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3		7.15	
D4		3.59	
D5		3.26	
e	1.10	1.20	1.30
E	9.80	9.90	10.00
E1	7.40	7.50	7.60
E2	0.30	0.40	0.50
E3		8.50	
E4		9.46	
H	11.50	11.68	11.85
H1	0.55	0.65	0.75
K	4.08	4.18	4.28
L	1.60	1.90	2.10
L1	0.50	0.70	0.90
L2	0.50	0.60	0.70
L3	1.00	1.20	1.30
L4	0.13	0.23	0.33
P	2.85	3.00	3.15
θ		10°REF	
aaa		0.20	
ccc		0.20	
ddd		0.25	
eee		0.20	